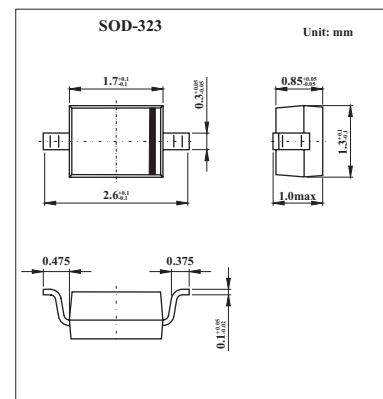


Schottky barrier Diodes

1PS76SB62

■ Features

- Ultra high swiching speed
- Very low capacitance
- High breakdown voltage
- Guard ring protected
- Two pin very small plastic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

PARAMATER	SYMBOL	MIN	MAX	UNIT
continuous reverse voltage	V_R		4	V
continuous forward current	I_F		20	mA
storage temperature	T_{stg}	-65	+150	$^\circ\text{C}$
junction temperature	T_j		125	$^\circ\text{C}$
operating ambient temperature	T_{amb}	-65	+125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

PARAMATER	SYMBOL	CONDITIONS	MAX	UNIT
forward voltage	V_F	$I_F = 2\text{ mA}; \text{Note 1}$	800	mV
reverse current	I_R	$V_R = 40\text{ V}; \text{note 1}$	1	$\mu\text{ A}$
diode capacitance	C_d	$V_R = 0\text{ V}; f = 1\text{ MHz}$	0.6	pF
thermal resistance from junction to ambient	R_{thj-a}		450	K/W

Note:

1.Pulse test: pulse width = 300 $\mu\text{ s}$; $\delta = 0.02$.

■ Marking

Marking	S6
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